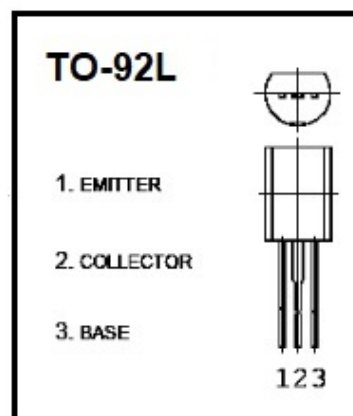


2SB764

- Complementary to: 2SD863
- Package: TO-92L

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector-base voltage	BV_{CBO}	-60	V
Collector-emitter voltage	BV_{CEO}	-50	V
Emitter-base voltage	BV_{EBO}	-5	V
Collector current	I_{CM}	-1	A
Collector Power Dissipation	P_C	900	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 ~ +150	°C



Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = -10\mu A, I_E = 0$	-60			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1mA, I_B = 0$	-50			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -10\mu A, I_C = 0$	-5			V
collector-base cut-off current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-1.0	μA
collector-emitter cut-off current	I_{CEO}	$V_{CE} = -40V, I_B = 0$			-1.0	μA
emitter-base cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-1.0	μA
DC current gain	H_{FE}	$V_{CE} = -2V, I_C = -50mA$	60		320	
	H_{FE1}	$V_{CE} = -2V, I_C = -1A$	30			
collector-emitter saturation voltage	V_{CESAT}	$I_C = -0.5A, I_B = -50mA$			-0.7	V
Base-Emitter Saturation Voltage	V_{BESAT}	$I_C = -0.5A, I_B = -50mA$			-1.2	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -50mA$		150		MHz

Classification of H_{FE}

Rank	D	E	F
Range	60-120	100-200	160-320